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1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection in a DSN0603-2 (SOD962-2) leadless ultra small Chip-Scale Package (CSP).

2. Features and benefits

- Average forward current $I_{F(AV)} \le 0.2 A$
- Reverse voltage V_R ≤ 30 V
- Low forward voltage typ. V_F = 310 mV
- Low reverse current typ. I_R = 0.33 μA
- Package height typ. 0.3mm

3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Ultra high speed switching
- LED backlight for mobile application

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{F(AV)}	average forward current	δ = 0.5; f = 20 kHz; $T_{amb} \le$ 140 °C; square wave	[1]	-	-	0.2	А
		δ = 0.5; f = 20 kHz; $T_{sp} \le$ 148 °C; square wave		-	-	0.2	A
V _R	reverse voltage	T _j = 25 °C		-	-	30	V
V _F	forward voltage	I_F = 10 mA; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C		-	310	390	mV
I _R	reverse current	V _R = 10 V; T _j = 25 °C; pulsed		-	0.33	2	μΑ
t _{rr}	reverse recovery time	I_F = 500 mA; I_R = 500 mA; $I_{R(meas)}$ = 100 mA; T_j = 25 °C		-	1.42	-	ns

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al_2O_3 , standard footprint.





30 V, 0.2 A low VF MEGA Schottky barrier rectifier

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode[1]		1][-] 2
2	Α	anode		sym001
			Transparent top view	
			DSN0603-2 (SOD962-2)	

^[1] The marking bar indicates the cathode.

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMEG3002ESF	DSN0603-2	Leadless ultra small package; 2 terminals; body $0.6 \times 0.3 \times 0.3$ mm	SOD962-2			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMEG3002ESF	K

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_R	reverse voltage	T _j = 25 °C		-	30	V
I _F	forward current	T _{sp} ≤ 145 °C; δ = 1		-	0.28	Α
I _{F(AV)}	average forward current	$\bar{\delta}$ = 0.5; f = 20 kHz; $T_{amb} \leq$ 140 °C; square wave	[1]	-	0.2	A
		δ = 0.5; f = 20 kHz; T _{sp} ≤ 148 °C; square wave		-	0.2	A
I _{FRM}	repetitive peak forward current	t_p = 1 ms; δ ≤ 0.25		-	1.5	Α
I _{FSM}	non-repetitive peak forward current	t_p = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	3.5	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	<u>[2]</u>	-	405	mW
			[3]	-	660	mW
			[1]	-	1200	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for anode and cathode 1 cm² each.

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient			[1][2]	-	-	310	K/W
			[1][3]	-	-	190	K/W
	ambient		[1][4]	-	-	105	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		[5]	-	-	40	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
- 2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for anode and cathode 1 cm² each.
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [5] Soldering point of anode tab.

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30 V, 0.2 A low VF MEGA Schottky barrier rectifier

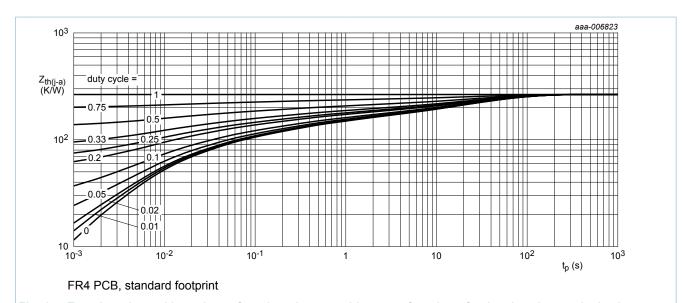
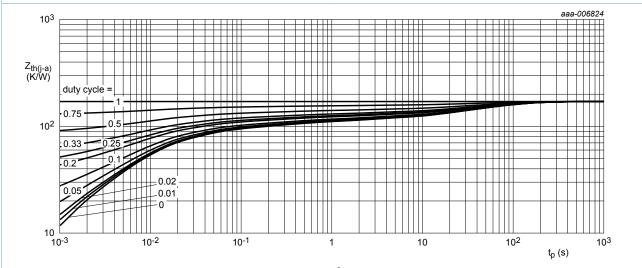


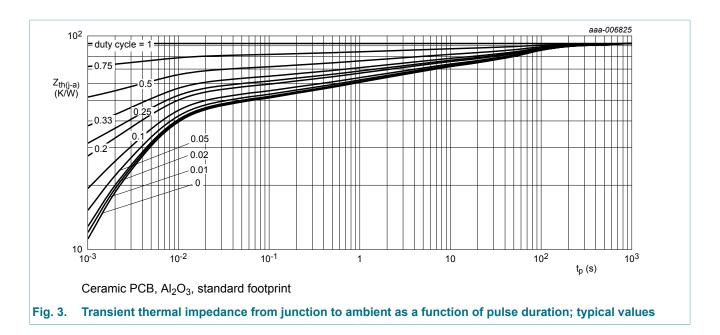
Fig. 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for anode and cathode 1 cm² each

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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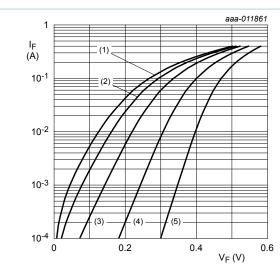
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)R}$	reverse breakdown voltage	I_R = 100 μ A; t_p = 300 μ s; δ = 0.02; T_j = 25 °C	30	-	-	V
V _F	forward voltage	I_F = 0.1 mA; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C	-	185	255	mV
		I_F = 1 mA; $t_p \le 300$ μs; $δ \le 0.02$; T_j = 25 °C	-	245	320	mV
		I_F = 10 mA; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C	-	310	390	mV
		I_F = 100 mA; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C	-	405	480	mV
		I_F = 200 mA; $t_p \le 300$ μs; $δ \le 0.02$; T_j = 25 °C	-	460	535	mV
I _R	reverse current	$V_R = 10 \text{ V}; T_j = 25 ^{\circ}\text{C}; \text{ pulsed}$	-	0.33	2	μA
		$V_R = 30 \text{ V}; T_j = 25 ^{\circ}\text{C}; \text{ pulsed}$	-	1.8	9	μA
C _d	diode capacitance	V _R = 1 V; f = 1 MHz; T _j = 25 °C	-	21	-	pF
		V _R = 10 V; f = 1 MHz; T _j = 25 °C	-	8	-	pF
t _{rr}	reverse recovery time	I_F = 500 mA; I_R = 500 mA; $I_{R(meas)}$ = 100 mA; T_j = 25 °C	-	1.42	-	ns

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pulsed condition

(1) $T_i = 150 \, ^{\circ}C$

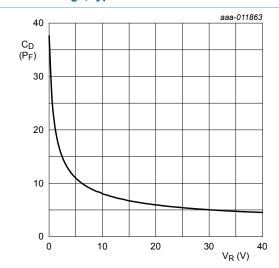
(2) $T_i = 125 \, ^{\circ}C$

(3) $T_j = 85 \, ^{\circ}C$

(4) $T_j = 25 \, ^{\circ}C$

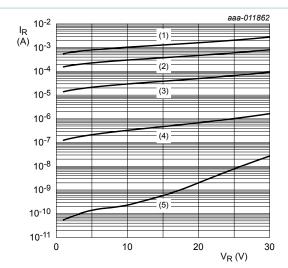
(5) $T_i = -40 \, ^{\circ}C$

Fig. 4. Forward current as a function of forward voltage; typical values



 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$

Fig. 6. Diode capacitance as a function of reverse voltage; typical values



pulsed condition

(1) $T_i = 150 \, ^{\circ}C$

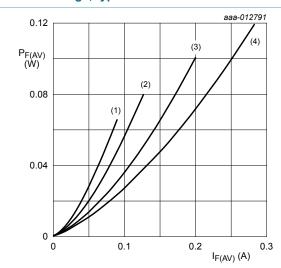
(2) $T_i = 125 \,^{\circ}\text{C}$

(3) $T_j = 85 \, ^{\circ}C$

(4) $T_j = 25 \, ^{\circ}C$

(5) $T_i = -40 \, ^{\circ}C$

Fig. 5. Reverse current as a function of reverse voltage; typical values



 $T_i = 150 \,{}^{\circ}\text{C}$

 $(1) \delta = 0.1$

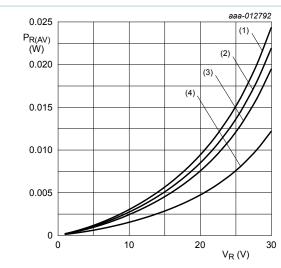
 $(2) \delta = 0.2$

 $(3) \delta = 0.5$

 $(4) \delta = 1$

Fig. 7. Average forward power dissipation as a function of average forward current; typical values

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 $T_i = 125 \,{}^{\circ}\text{C}$

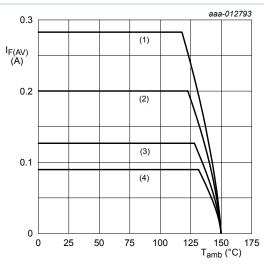
 $(1) \delta = 1$

 $(2) \delta = 0.9$

 $(3) \delta = 0.8$

 $(4) \delta = 0.5$

Fig. 8. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

T_i = 150 °C

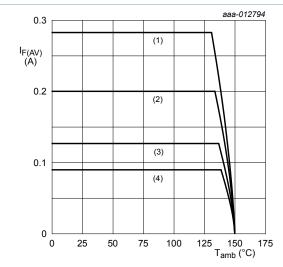
(1) δ = 1; DC

(2) $\delta = 0.5$; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

(4) δ = 0.1; f = 20 kHz

Fig. 9. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for anode and cathode 1 cm² each

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 $T_j = 150 \,{}^{\circ}\text{C}$

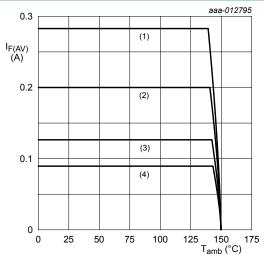
(1) δ = 1; DC

(2) $\delta = 0.5$; f = 20 kHz

(3) $\delta = 0.2$; f = 20 kHz

(4) δ = 0.1; f = 20 kHz

Fig. 10. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al₂O₃, standard footprint

 $T_i = 150 \, ^{\circ}C$

(1) δ = 1; DC

(2) δ = 0.5; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

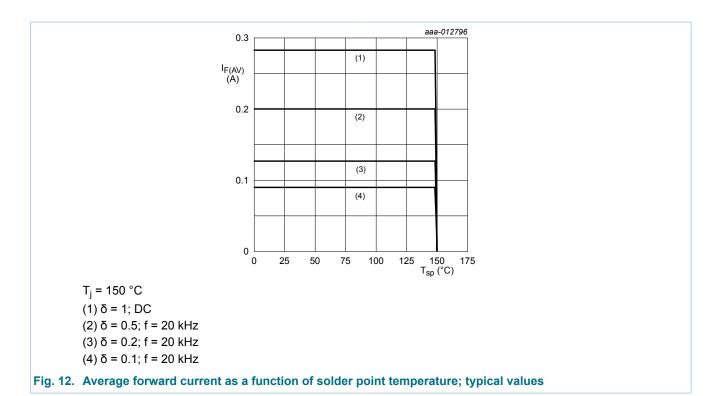
(4) δ = 0.1; f = 20 kHz

Fig. 11. Average forward current as a function of ambient temperature; typical values

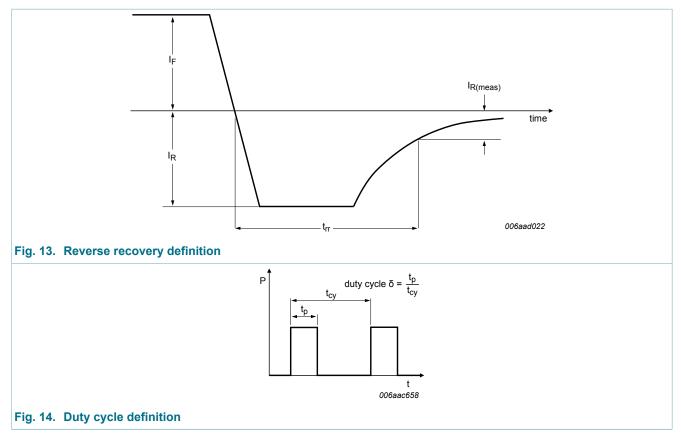
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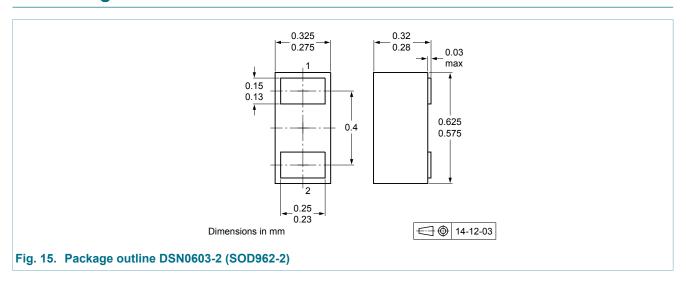
11. Test information



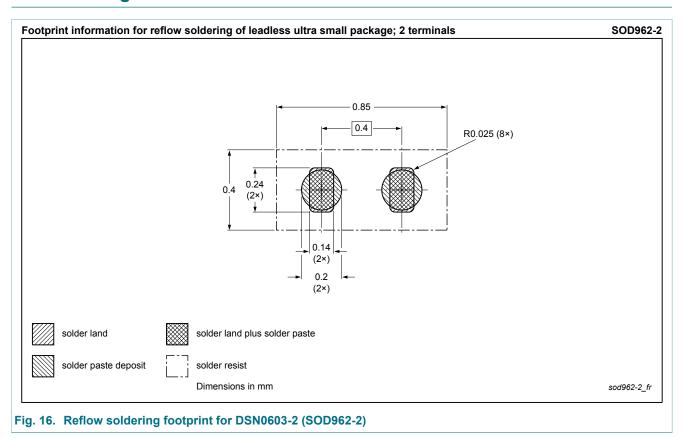
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The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG3002ESF v.2	20150217	Product data sheet	-	PMEG3002ESF v.1
Modifications:	 Product status char 	nged		
PMEG3002ESF v.1	20140415	Preliminary data sheet	-	-

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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